NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **UFT30-28** is Designed for Class A and B Power Ampliifiers Operating up to 500 MHz.

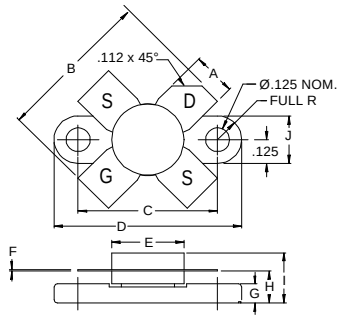
FEATURES:

- **P_G =** 7.0 dB min. at 25 W/400 MHz
- η_D = 60 % Typical
- ***Omnigold***™ Metalization System

MAXIMUM RATINGS

I_D	5.0 A
V_{DDS}	65 V
V_{GS}	±40 V
P_{DISS}	100 W @ T_C = 25 ^{O}C
T_J	-65 ^{O}C to +200 ^{O}C
T_{STG}	-65 ^{O}C to +150 ^{O}C
θ_{JC}	1.8 ^{O}C/W

PACKAGE STYLE .380 4L FLG.



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.220 / 5.59	.230 / 5.84
B	.785 / 19.94	
C	.720 / 18.29	.730 / 18.54
D	.970 / 24.64	.980 / 24.89
E		.385 / 9.78
F	.004 / 0.10	.006 / 0.15
G	.085 / 2.16	.105 / 2.67
H	.160 / 4.06	.180 / 4.57
I		.280 / 7.11
J	.240 / 6.10	.255 / 6.48

ORDER CODE: ASI10666

CHARACTERISTICS T_C = 25 ^{O}C

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
V_{DSS}	I_{DS} = 10 mA			60			V
I_{DSS}	V_{DS} = 28 V					4.0	mA
I_{GSS}	V_{GS} = 20 V					1.0	µA
V_{GS}	V_{DS} = 10 V	I_D = 25 mA		1.0		6.0	V
G_{FS}	V_{DS} = 10 V	I_D = 500 mA		500			mMho
C_{ISS} C_{OSS} C_{RSS}	V_{DS} = 28 V	V_{GS} = 0 V	f = 1.0 MHz		46 33 6.0		pF
P_G η_D	V_{DD} = 28 V f = 400 MHz	I_{DQ} = 25 mA	P_{OUT} = 25 W	7.0 60			dB %